Form PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)	Attorney Docket No. 5308-395	Serial No. 10/790406 To be assigned
	Applicant: O'Loughlin et al.	
	Filing Date: Concurrently herewith	GAU: Uknown

U.S. PATENT DOCUMENTS

Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
EK	1	US2003/0079689A1	5/1/03	Sumakeris et al.	118	725	

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)

OTHER DOCUMENTS

EK	2	Okada et al. "Crystallographic defects under surface morphological defects of 4H-SiC homoepitaxial films," ICSCRM 2003 Poster Sessions.
EK	3	Wahab et al. "Influence of epitaxial growth and substrate-induced defects on the breakdown of 4H-SiC Schottky diodes," *Applied Physics Letters*, Vol. 76, No. 19, May 8, 2000, pp. 2725-7.
	4	U.S. Application Serial No. 10/414,787 entitled *Methods and Apparatus for Controlling Formation of Deposits in a Deposition System and Depositions Systems and Methods Including the Same*, filed April 16, 2003.
	5	U.S. Application Serial No. 09/756,548, titled *Gas Driven Rotation Apparatus and Method for Forming Silicon Carbide Layers*, filed January 8, 2001.
	6	U.S. Application Serial No. 10/117,858, titled *Gas Driven Planetary Rotation Apparatus and Methods for Forming Silicon Carbide Layers*, filed April 8, 2002.

Examiner: EK Date Considered: 7/10/06

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute form 1449A/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/790,406
				Filing Date	March 1, 2004
				First Named Inventor	Michael John O'Loughlin
				Group Art Unit	1765
(use as many sheets as necessary)				Examiner Name	Nadine Georgianna Norton
Sheet	1	of	1	Attorney Docket Number	5308-395

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
GC	1.	US-2005/0064723		Sumakeris	03-24-2005
GC	2.	US-2003/0079689		Sumakeris et al.	05-01-2003
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Translation
		Office	Number	Kind Code (if known)			
GC	3.	JP	2000-053498		Toyota Cwentral Res & Dev Lab, Inc.	02-22-2000	Abstract
GC	4.	WO	97/01658		Okmetic, Ltd.	01-16-1997	

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
GC	5.	Ellison et al. "Epitaxial Growth of SiC in a Chimney CVD Reactor" *Journal of Crystal Growth* 236: 225-238 (2002)	
GC	6.	International Search Report and the Written Opinion of the International Searching Authority for International patent application no. PCT/US2004/038895 mailed on June 1, 2005	
GC	7.	Kimoto et al. "Homoepitaxial Growth of 4H-SiC(0 3 3 8) and Nitrogen Doping by Chemical Vapor Deposition" *Journal of Crystal Growth* 249: 208-215 (2003)	
GC	8.	Konstantinov et al. "The Mechanism for Cubic SiC Formation on Off-Oriented Substrates" *Journal of Crystal Growth* 178: 495-504 (1997)	
GC	9.	Mills "Wide Bandgaps Show Power Pedigree in San Francisco" *Meeting Report* 11(5): 46-51 (1998)	
GC	10.	Nakazawa et al. "High-purity 4H-Sic Epitaxial Growth by Hot-Wall Chemical Vapor Deposition" *Journal of Crystal Growth* 237-239: 1213-1218 (2002)	
GC	11.	Okada et al. "Correspondence Between Surface Morphological Faults And Crystallographic Defects In 4H-SiC Homoepitaxial Film" *Jpn J Appl Physics* 41: 6320-6326 (2002)	
GC	12.	Wahab et al. "Influence of Epitaxial Growth and Substrate-Induced Defects on the Breakdown of 4H-SiC Schottky Diodes" *Applied Physics Letters* 76(19): 2725-2727 (2000)	

Examiner Signature	GC	Date Considered	7/10/06

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